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PLASMA PROCESSOR AND PLASMA PROCESSING METHOD

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#### ABSTRACT

PROBLEM TO BE SOLVED: To uniformly perform plasma processing on an entire face of a substrate.

SOLUTION: A plasma processor recesses a substrate placement face 11a of a substrate placement stage 11, connects a high-frequency power supply 12 to the substrate placement stage 11, provides a temperature controller 13 for performing temperature control of the substrate placement stage 11, provides a heat-conducting gas supply hole 14 on the substrate placement stage 11, provides a heat-conducting gas supplier 18 for supplying He gas to the heat-conducting gas supplying hole 14, provides an insulator 19 at the outer circumference part of the substrate placement stage 11, and mounts the insulator 19 in a processing chamber 20. The processor mounts an elevation plate 21 in the processing chamber 20 via a bellows 22, provides a spring 23 between the elevation plate 21 and the processing chamber 20, provides an air cylinder 24 for elevating the elevation plate 21, mounts a substrate clamp 25 on the elevation plate 21, and mounts a counter electrode 26 opposite to the substrate placement stage 11 in the processing chamber 20.

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